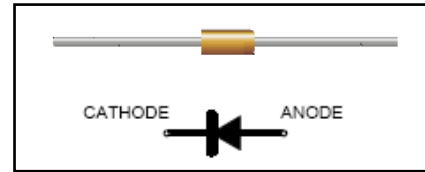


# Bi-directional trigger diodes

- . 500mW DO-35
- . Glass silicon
- . We declare that the material of product compliance with RoHS requirements.

DB-4



## Product Characteristic

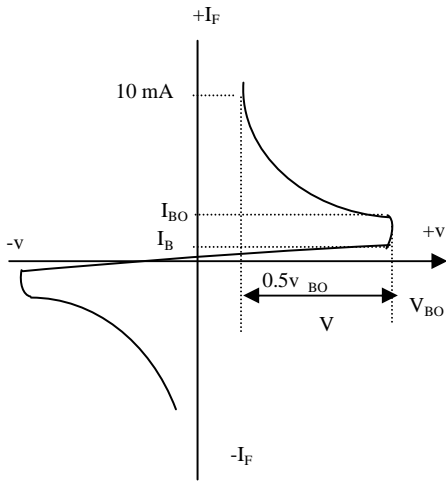
Symbol	Parameter	Test Condition	TYPE	Min	Typ	Max	Unit
$V_{BO}$	Breakdown Voltage	$I=I_{BO}$	DB-3 DB-4 DB-6	28 35 56	32 40 60	36 45 70	V
$ +V_{BO}  -  -V_{BO} $	Breakover Voltage Symmetry		DB-3 DB-4 DB-6			3 3 4	V
$ \pm \Delta V $	Dynamic Breakover Voltage	$\Delta I =  I_{BO} \text{ to } I_F = 10\text{mA} $	DB-3 DB-4 DB-6	5 5 10			V
$V_O$	Output Voltage			5			V
$I_{BO}$	Breakdown Current	$V=V_{BO}$				100	$\mu\text{A}$
$t_r$					1.5		$\mu\text{S}$
$I_B$	Leakage Current	$V_B=0.5V_{BO} \text{ (max)}$				10	$\mu\text{A}$

## Limiting Values

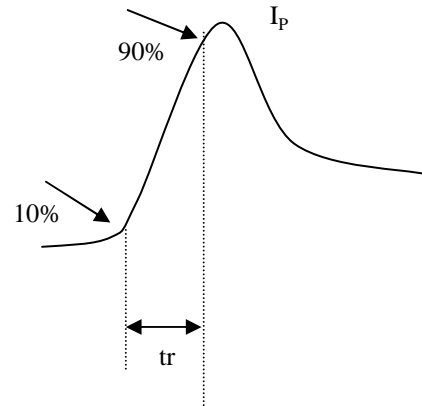
Symbol	Parameter		Value	Unit
$P_c$	Power Dissipation	$T_a=50$	150	mW
$I_{Fmax}$	Peak Pulse Current	$t_p=10\mu\text{s}$ 120PPS $T_a$ 40	DB-3 2.0 DB-4 2.0 DB-6 16	A
$T_r$	Storage and Operating		-40 to 125	
$T_j$	Junction Temperatuer Range.		-40 to 110	

## Characteristic Curves

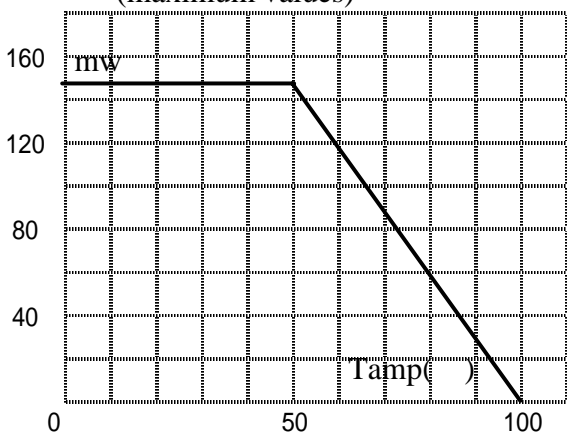
Current-voltage characteristics



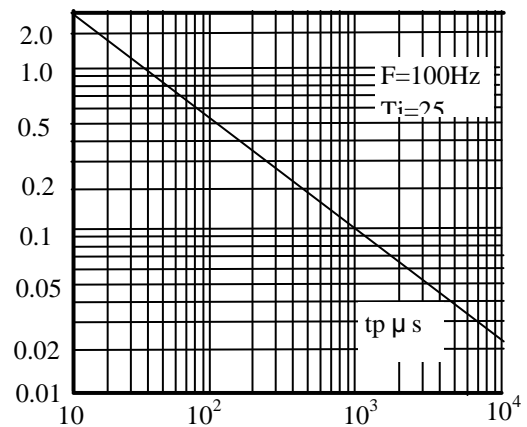
Test circuit see diagram 2  
Adjust R for  $I=0.5A$



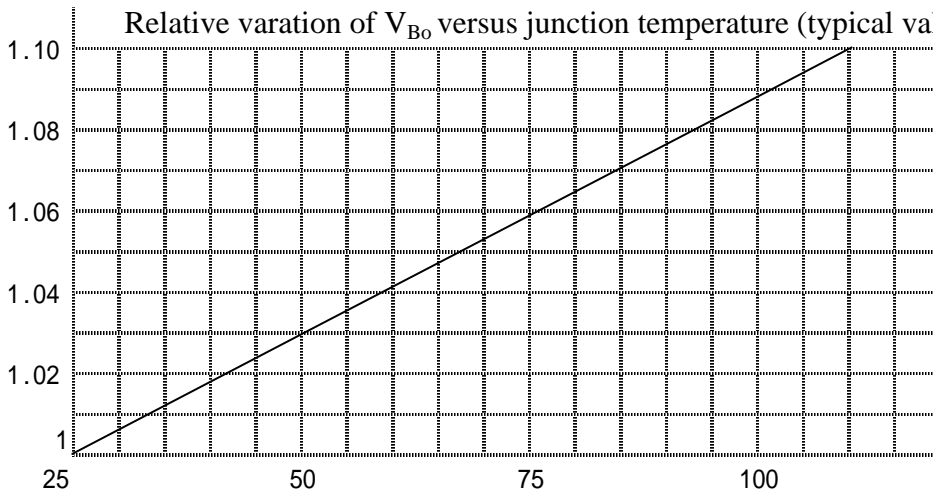
Power dissipation versus ambient temperature  
(maximum values)



Peak pulse Current versus pulse duration  
(maximum values)



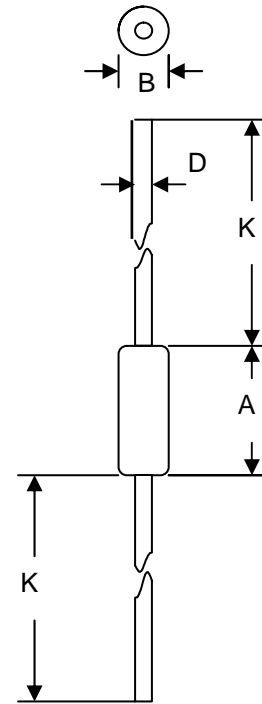
Relative variation of  $V_{BO}$  versus junction temperature (typical values)



### Package Dimensions in inches and (millimeters)

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	3.6	4.0	0.14	0.157
B	1.6	2.0	0.063	0.079
D	0.4	0.6	0.016	0.024
K	28	30	1.102	1.181

D0-35

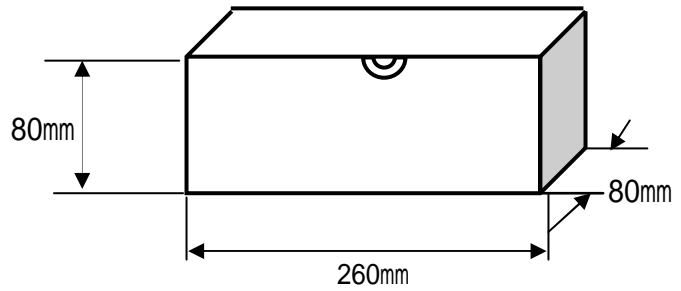


D0-35

## Packing

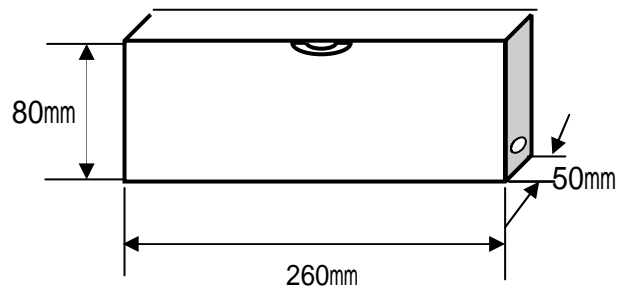
### Taping / Box(T52)

Tape Inner Box:5000pcs/each



### Taping / Box(T26)

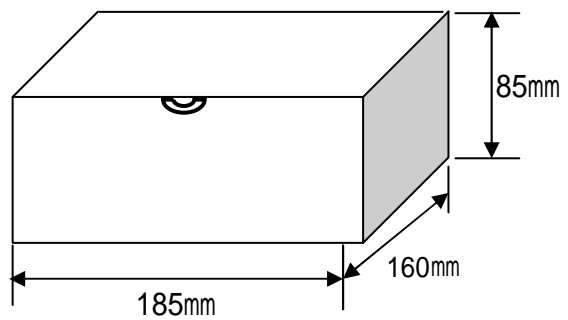
Tape Inner Box:5000pcs/each



### Bulk

500pcs/bag

10000pcs /each



### Reel (T52 )

10000pcs/卷

